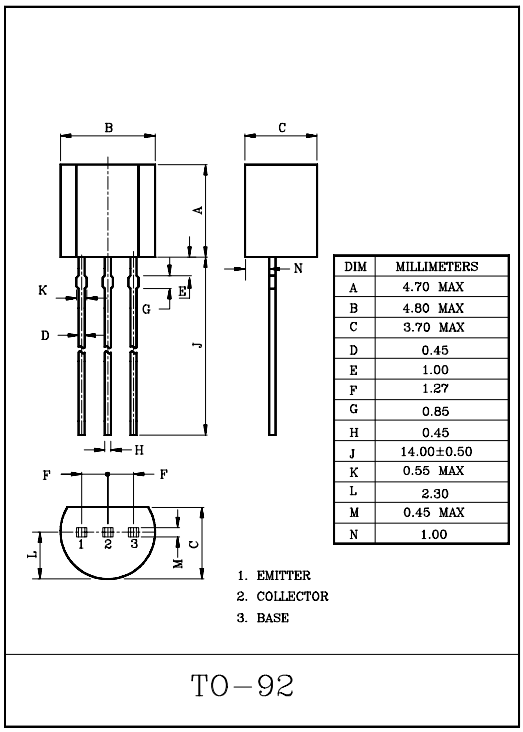
KTA1266L

EPITAXIAL PLANAR PNP TRANSISTOR

LOW NOISE AMPLIFIER APPLICATION.

FEATURES

- Excellent h_{FE} Linearity
  : $h_{FE}(2)$=80(Typ.) at V_{CE}=-6V, I_C=-150mA
  : $h_{FE}(I_C$=0.1mA)/$h_{FE}(I_C$=2mA)=0.95(Typ.).
- Low Noise : NF=0.2dB(Typ.). f=(1kHz).
- Complementary to KTC3198L.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

TO-92

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-150	mA
Emitter Current	I_E	150	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-50V, I_E=0	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-0.1	μA
DC Current Gain	$h_{FE}(1)$ (Note)	V_{CE}=-6V, I_C=-2mA	70	-	400	
	$h_{FE}(2)$	V_{CE}=-6V, I_C=-150mA	25	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA	-	-0.1	-0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-10mA	-	-	-1.1	V
Transition Frequency	f_T	V_{CE}=-10V, I_E=1mA	80	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	4.0	7.0	pF
Base Intrinsic Resistance	rbb′	V_{CB}=-10V, I_E=1mA, f=30MHz	-	30	-	Ω
Noise Figure	NF(1)	V_{CE}=-6V, I_C=-0.1mA, f=100Hz, Rg=10kΩ	-	0.5	6.0	dB
	NF(2)	V_{CE}=-6V, I_C=-0.1mA, f=1kHz, Rg=10kΩ	-	0.2	3.0	

Note : $h_{FE}(1)$ Classification O:70~140, Y:120~240, GR:200~400